

< X/Ku band internally matched power GaAs FET >

MGFK37V4045

14.0 - 14.5 GHz BAND / 5.5W

DESCRIPTION

The MGFK37V4045 is an internally impedance-matched GaAs power FET especially designed for use in 14.0 – 14.5 GHz band amplifiers. The hermetically sealed metal-ceramic package guarantees high reliability.

FEATURES

Internally matched to 50(ohm) system

- Flip-chip mounted
 High output power
 - P1dB=5.5W (TYP.) @f=14.0 14.5GHz
- High linear power gain
 - GLP=5.5dB (TYP.) @f=14.0 14.5GHz
- High power added efficiency
 - P.A.E.=17% (TYP.) @f=14.0 14.5GHz

APPLICATION

• 14.0 - 14.5 GHz band power amplifiers

QUALITY GRADE

• IG

RECOMMENDED BIAS CONDITIONS

• VDS=10V • ID=2.4A Refer to Bias Procedure

Absolute maximum ratings (Ta=25°C)

Symbol	Parameter	Ratings	Unit
VGDO	Gate to drain breakdown voltage	-15	V
VGSO	Gate to source breakdown voltage	-15	V
ID	Drain current	6600	mA
IGR	Reverse gate current	-17.5	mA
IGF	Forward gate current	35	mA
PT *1	Total power dissipation	42.8	W
Tch	Cannel temperature	175	°C
Tstg	Storage temperature	-65 to +175	°C

*1 : Tc=25°C

OUTLINE DRAWING Unit: millimeters (inches) 16.0 ± 0.3 (0.630 ± 0.012) 2MIN. (0.079MIN.) 0.6 ± 0.15 (0.024 ± 0.006) (0.256+0.004) 6.5 +0.1 R1.25 ທ (R0.049)ທີ່ 2MIN. (0.079MIN.) (3) 0.6 ± 0.15 (0.024 ± 0.006) 9.0 (0,354) 13.0 ± 0.2 (0.512 ± 0.008) (0.004) (0.043)2.9 ± 0.4 114 ± 0.016) 10.0 (0.394) (i) GATE 2 SOURCE 3 DRAIN GF-14

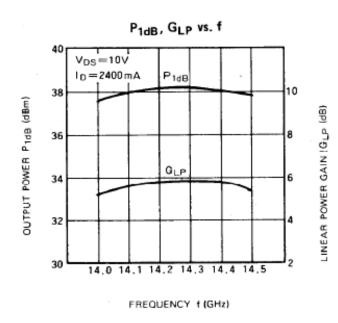
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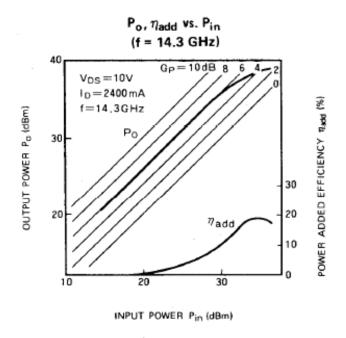
Electrical characteristics (Ta=25°C)

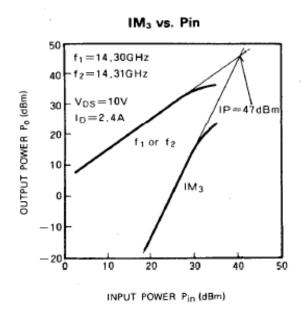
Symbol	Parameter	Test conditions		Limits		
			Min.	Тур.	Max.	
IDSS	Saturated drain current	VDS=3V,VGS=0V	3600	5200	6600	mA
gm	Transconductance	VDS=3V,ID=2400mA	1200	1700	-	mS
VGS(off)	Gate to source cut-off voltage	VDS=3V,ID=20mA	-2	-	-5	V
P1dB	Output power at 1dB gain compression	VDS=10V,ID(RF off)=2400mA	36.5	37.4	-	dBm
GLP	Linear Power Gain	f=14.0 - 14.5GHz	4.5	5.5	-	dB
PAE	Power added efficiency		-	17	-	%
Rth(ch-c) *2	Thermal resistance	delta Vf method	-	-	3.5	°C/W

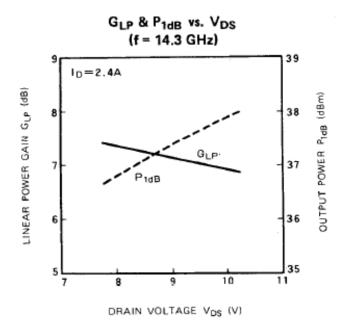
*2 : Channel-case

MGFK37V4045 TYPICAL CHARACTERISTICS

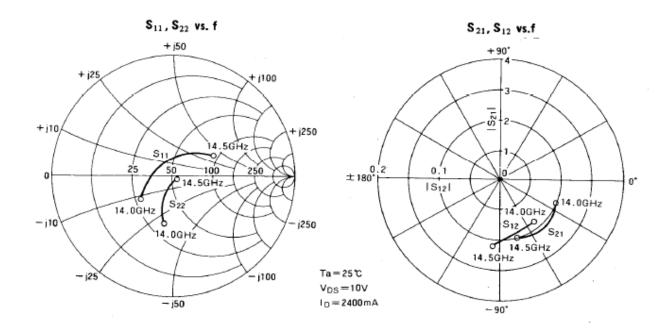








MGFK37V4045 S-parameters(Ta=25deg.C , VDS=10(V),IDS=2400(mA))



	S Parameters(Typ.)							
(GHz)	S11		S21		S12		S22	
	Magn.	Angle(deg.)	Magn.	Angle(deg.)	Magn.	Angle(deg.)	Magn.	Angle(deg.)
14.0	0.336	-143	1.950	-24	0.074	-52	0.396	-99
14.1	0.201	-168	2.018	-34	0.081	-64	0.314	-104
14.2	0.128	145	2.042	-43	0.083	-72	0.228	-103
14.3	0.132	87	2.055	-54	0.094	-83	0.167	-99
14.4	0.247	47	2.018	-64	0.099	-90	0.096	-100
14.5	0.398	26	1.950	-75	0.109	-98	0.053	-49

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